风光欣技术资料

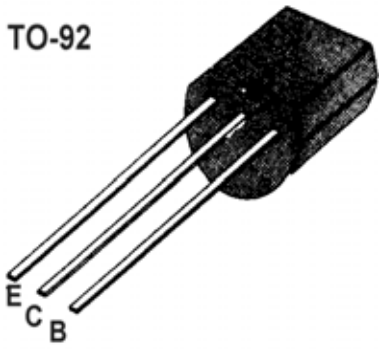
A933

—PNP silicon —

■■**APPLICATION**：General Purpose Applications.

■■**MAXIMUM RATINGS**（Ta＝25℃）

PARAMETER	SYMBOL	RATING	UNIT
Collector-base voltage	V_{CBO}	-50	V
Collector-emitter voltage	V_{CEO}	-40	V
Emitter-base voltage	V_{EBO}	-5	V
Collector current	I_C	-150	A
Collector Power Dissipation	P_C	300	W
Junction Temperature	T_J	150	℃
Storage Temperature Range	Tstg	－55~150	℃



■■**ELECTRICAL CHARACTERISTICS**（Ta=25℃）

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITION
DC Current Gain	h_{FE}	120		820		V_{CE}= -6V，Ic= -1mA
Collector Cut-off Current	I_{CBO}			-0.5	μA	V_{CB}= -30V，I_E=0
Emitter Cut-off Current	I_{EBO}			-0.5	μA	V_{EB}= -3V，Ic=0
Collector-Base Breakdown Voltage	BV_{CBO}	-50			V	Ic= -0.02mA，I_E=0
Collector-Emitter Breakdown Voltage	BV_{CEO}	-40			V	Ic= -1mA，I_B=0
Emitter-Base Breakdown Voltage	BV_{EBO}	-5			V	I_E= -0.02mA，Ic=0
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$			-0.4	V	Ic= -50mA，I_B= -5mA
Base-Emitter Saturation Voltage	$V_{BE(sat)}$			-1.1	V	Ic= -50mA，I_B= -5mA
Gain bandwidth product	f_T		180		MHz	Ic= -2mA，V_{CE}= -12V
Common Base Output Capacitance	Cob		4		PF	V_{CB}= -10V，I_E=0，f = 1MHz

■■h_{FE} **Classification And Marking**

Classification	Q	R	S	E
h_{FE}	120～270	180～390	270～560	390～820